TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

# **TPC6201**

HDD Motor Drive Applications Notebook PC Applications Portable Equipment Applications

• Low drain-source ON resistance: RDS (ON) = 80 m $\Omega$  (typ.)

• High forward transfer admittance:  $|Y_{fs}| = 3.8 \text{ S (typ.)}$ 

• Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$ 

• Enhancement-model:  $V_{th}$  = 1.3 to 2.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

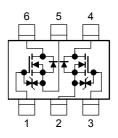
## **Maximum Ratings (Ta = 25°C)**

С	characteristics	Symbol	Rating	Unit	
Drain-source	voltage	$V_{DSS}$	30	V	
Drain-gate vo	ltage (R <sub>GS</sub> = 20 kΩ)	$V_{DGR}$	30	V	
Gate-source	voltage	$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	ΙD	2.5	Α	
	Pulse (Note 1)	I <sub>DP</sub>	10	A	
Drain power dissipation (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	P <sub>D</sub> (1)	0.9	W	
	Single device value at dual operation (Note 3b)	P <sub>D</sub> (2)	0.76		
Drain power dissipation (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	P <sub>D</sub> (1)	0.4	W	
	Single device value at dual operation (Note 3b)	P <sub>D</sub> (2)	0.31		
Single pulse a	avalanche energy (Note 4)	E <sub>AS</sub>	1.0	mJ	
Avalanche cu	rrent	I <sub>AR</sub>	1.25	Α	
Repetitive ava	alanche energy (Note 5)	E <sub>AR</sub>	0.16	mJ	
Channel temp	perature	T <sub>ch</sub>	150	°C	
Storage temp	erature range	T <sub>stg</sub>	-55 to 150	°C	

# 

Weight: 0.011 g (typ.)

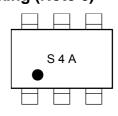
# **Circuit Configuration**



#### **Thermal Characteristics**

Chara	Symbol	Max	Unit		
Thermal Resistance (channel-to-ambient) (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	R <sub>th (ch-a)</sub> (2)	139	°C/W	
	Single device value at dual operation (Note 3b)	R <sub>th (ch-a)</sub> (2)	165		
Thermal Resistance	(Note 3a		310	°C/W	
(channel-to-ambient) (t = 5 s) (Note 2b)	Single device value at dual operation (Note 3b)	R <sub>th (ch-a)</sub> (2)	400	C/VV	

# Marking (Note 6)



Note: (Note 1), (Note 2), (Note 3), (Note 4), (Note 5), (Note 6) Please see next page.

This transistor is an electrostatically sensitive device. Please handle it with caution.

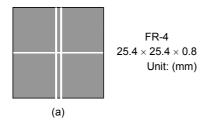
## **Electrical Characteristics (Ta = 25°C)**

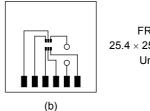
Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ	
Drain cut-OFF current		I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	μΑ	
Drain-source breakdown voltage		V <sub>(BR) DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V <sub>(BR) DSX</sub>	$I_D = 10$ mA, $V_{GS} = -20$ V	15	_	_	V	
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.3	_	2.5	V	
Drain-source ON resistance		R <sub>DS</sub> (ON)	$V_{GS} = 4.5 \text{ V}, I_D = 1.3 \text{ A}$	_	128	145	mΩ	
		R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, I_D = 1.3 \text{ A}$	_	80	95		
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.3 A	1.25	3.8	_	S	
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	170	_	pF	
Reverse transfer capacitance		C <sub>rss</sub>		_	25	_		
Output capacitance		Coss	-		40	_		
Switching time	Rise time	t <sub>r</sub>	ACS 0 A D = 1.3 Y	_	2.4	_	ns	
	Turn-ON time	t <sub>on</sub>		_	8	_		
	Fall time	t <sub>f</sub>		_	2	_		
	Turn-OFF time	t <sub>off</sub>	$V_{DD} \simeq 15 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \mu \text{s}$	_	11	_		
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V,	_	4.7			
Gate-source charge		Q <sub>gs</sub>	$I_D = 2.5 \text{ A}$	_	3.4	_	nC	
Gate-drain ("miller") charge		$Q_{gd}$		_	1.3	_		

# Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Pulse drain reverse current	(Note 1)	I <sub>DRP</sub>	_	_	_	10	Α
Forward voltage (diode)		V <sub>DSF</sub>	$I_{DR} = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$			-1.2	V

- Note 1: Please use devices on condition that the channel temperature is below 150°C.
- Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)
  - (b) Device mounted on a glass-epoxy board (b) (t = 5 s)

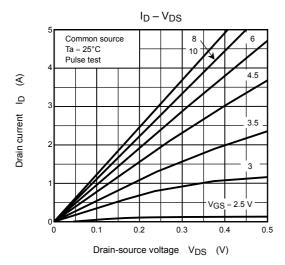


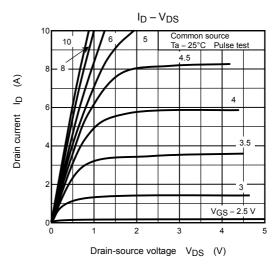


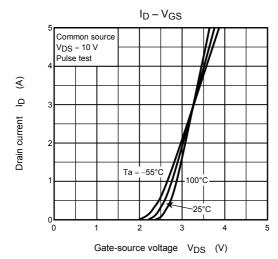
FR-4  $25.4\times25.4\times0.8$ Unit: (mm)

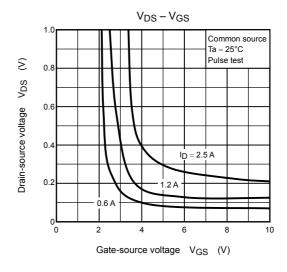
- Note 3: (a) Single-device operation; values of PD (1) and Rth (ch-a) (1) for a single device during single-device operation
  - (b) Dual operation; values of  $P_D$  (2) and  $R_{th\ (ch-a)}$  (2) for a single device during dual operation
- Note 4:  $V_{DD} = 24$  V,  $T_{ch} = 25$ °C (initial), L = 0.5 mH,  $R_G = 25$   $\Omega$ ,  $I_{AR} = 1.25$  A
- Note 5: Repetitive rating; pulse width limited by maximum channel temperature
- Note 6: Black round marking "•" locates on the left lower side of parts number marking "S4A" indicates terminal No.1.

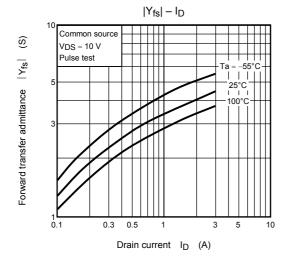
2

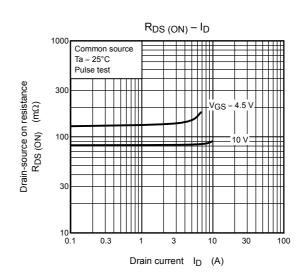




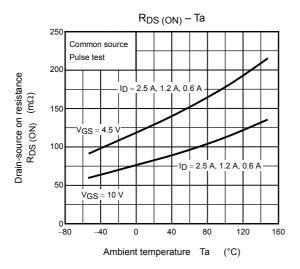


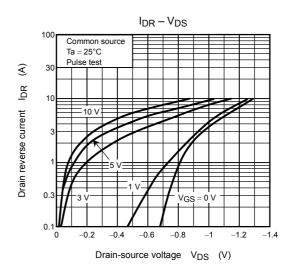


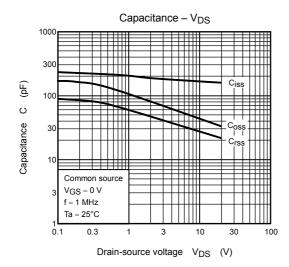


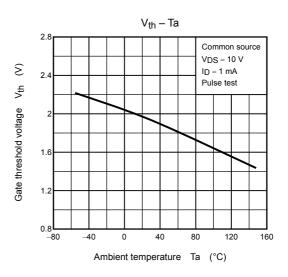


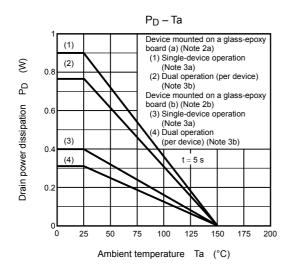
3

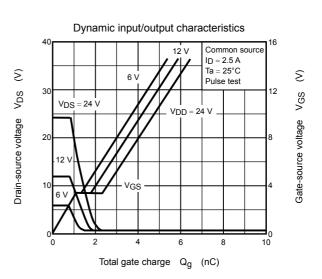




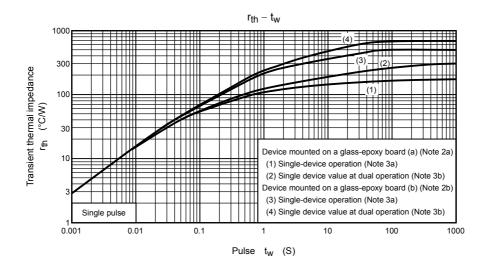




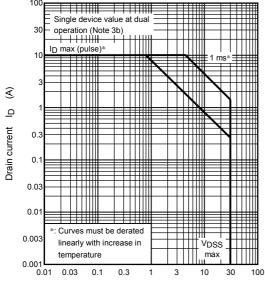




4







Drain-source voltage V<sub>DS</sub> (V)

#### **RESTRICTIONS ON PRODUCT USE**

000707EAA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
  rights of the third parties which may result from its use. No license is granted by implication or otherwise under
  any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.